

FIG.1A

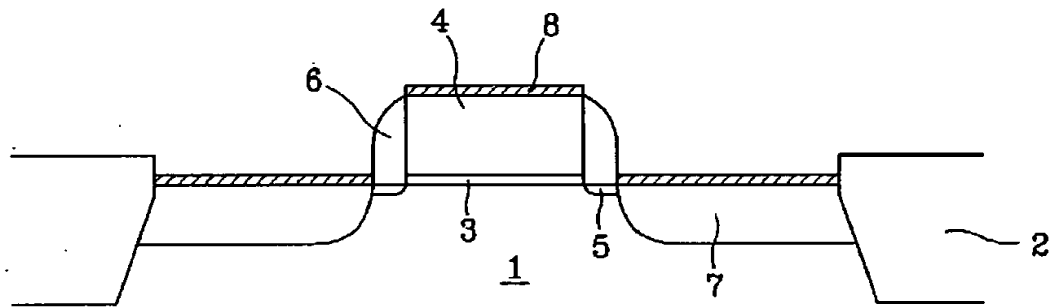


FIG.1B

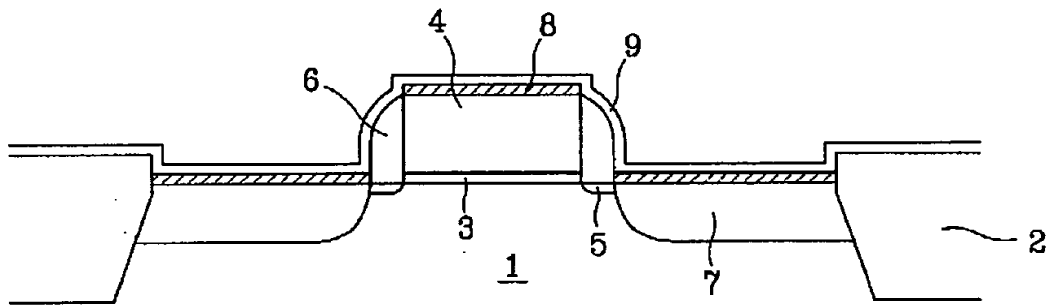


FIG.1C

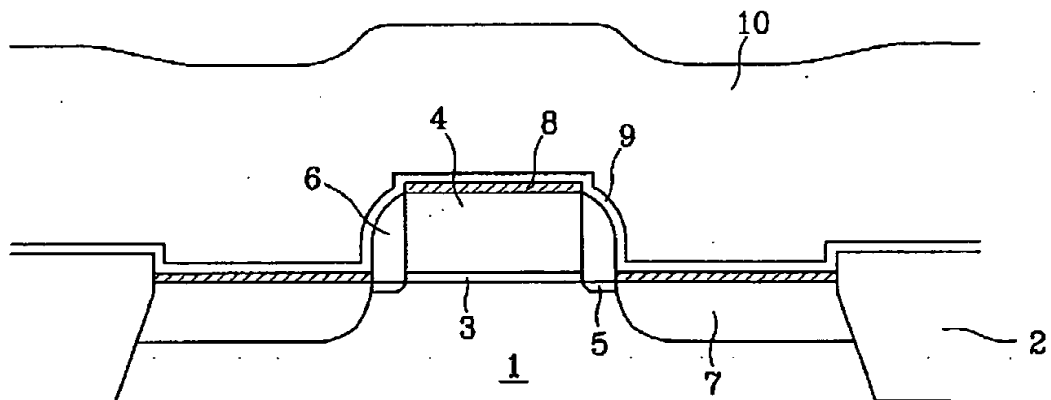


FIG.2A

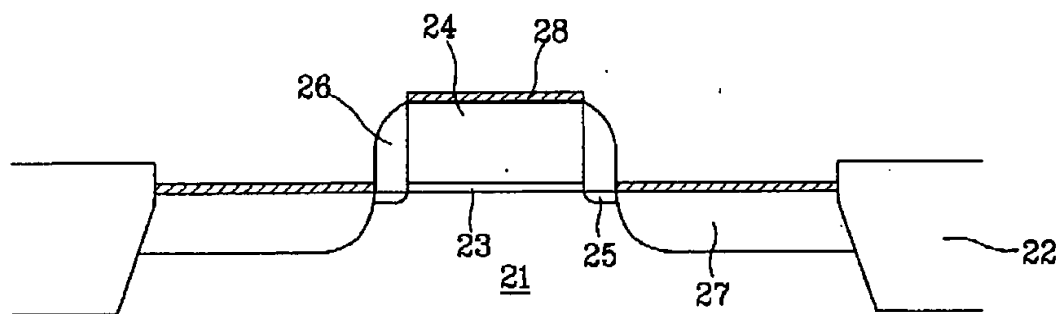
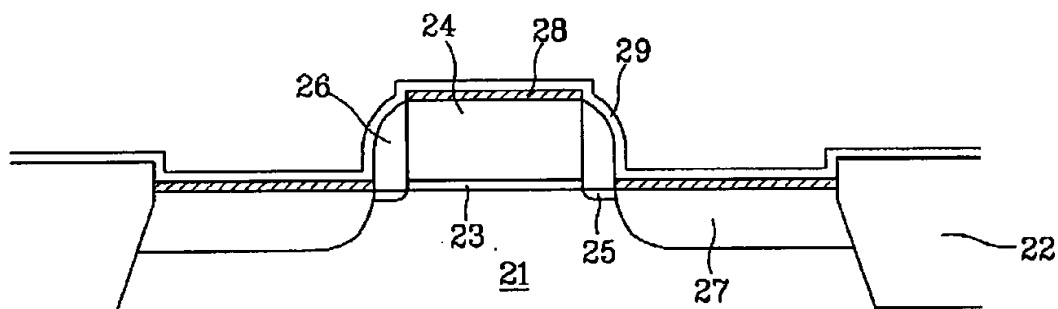


FIG.2B



A cross-sectional view of a semiconductor device. A central channel region (21) is defined by a gate stack (24, 28) on top. The channel is flanked by side gate regions (26, 29) and a central gate region (23). The device is embedded in a substrate (22). Arrows indicate a downward force or pressure applied to the top surface.